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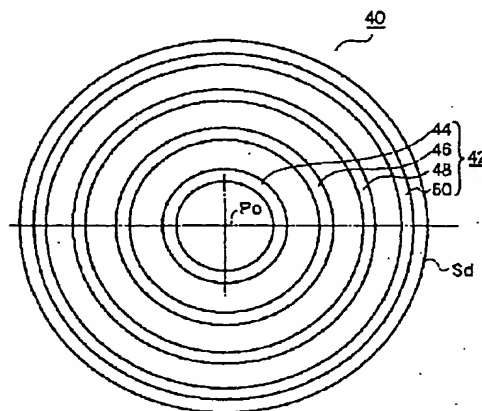
**H01L 21/205****C23C 16/458****H01L 21/31****H01L 21/68**(21) Application number: **2000214348**(22) Date of filing: **14.07.00**(71) Applicant: **MITSUI ENG & SHIPBUILD CO LTD  
ADMAP INC**(72) Inventor: **KAWAMOTO SATOSHI**(54) **WAFER HOLDER FOR VERTICAL CVD**

(57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a wafer holder for a vertical CVD wherein deformation of a wafer processing holder itself is less for less slip of a silicon wafer while the wafer holder is manufactured of CVD-SiC for high rigidity and heat resistance, resulting in less slip and good productivity.

**SOLUTION:** The wafer holder for vertical CVD is provided which is used for manufacturing a semiconductor device while a plurality of wafers are horizontally held side by side and inserted into the CVD device. The wafer holder for vertical CVD is provided with a rib on its upper surface for preventing deformation of the wafer holder while a wafer is held horizontally.

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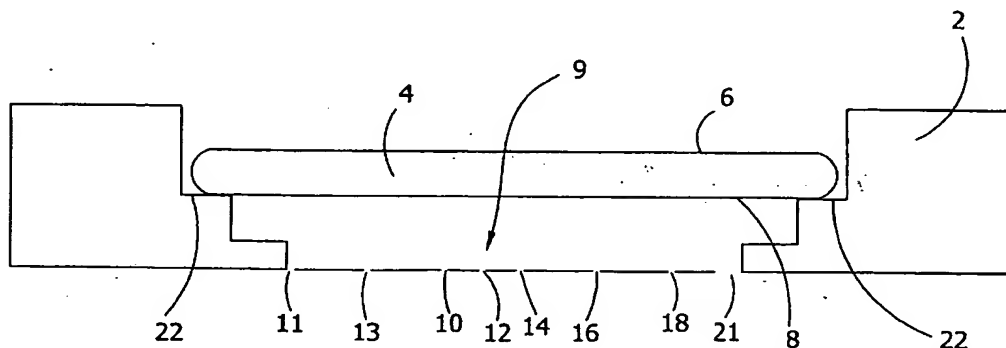
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(54) Title: **MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS**



(57) Abstract: A modified susceptor for use in an epitaxial deposition apparatus and process is disclosed. The modified susceptor has an inner annular ledge capable of supporting a semiconductor wafer and has a plurality of holes in the surface to allow cleaning gas utilized during an epitaxial deposition process to pass through the susceptor and contact substantially the entire back surface of the semiconductor wafer and remove a native oxide layer. Also, the plurality of holes on the susceptor allows dopant atoms out-diffused from the back surface during the epitaxial deposition process to be carried away from the front surface in an inert gas stream and into the exhaust such that autodoping of the front surface is minimized.



WO 01/86034 A2

## MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS

### BACKGROUND OF THE INVENTION

5 The present invention relates to a modified susceptor for use in a chemical vapor deposition process. More particularly, the present invention relates to a modified susceptor having a plurality of holes for use in an epitaxial deposition reactor and process such that autodoping of the front surface of a semiconductor wafer and discontinuous silicon growth on the back surface of the semiconductor wafer is significantly reduced or eliminated.

10 In the production of single silicon crystals grown by the Czochralski method, polycrystalline silicon is first melted within a quartz crucible with or without dopant. After the polycrystalline silicon has melted and the temperature equilibrated, a seed crystal is dipped into the melt and subsequently extracted to form a single crystal silicon ingot while the quartz crucible is rotated. The single crystal silicon ingot is  
15 subsequently sliced into individual semiconductor wafers which are subjected to several processing steps including lapping/grinding, etching, and polishing to produce a finished semiconductor wafer having a front surface with specular gloss. To prepare the finished wafer for device manufacturing, the wafer may be subjected to a chemical vapor deposition process such as an epitaxial deposition process to grow a thin layer  
20 of silicon generally between about 0.1 and about 200 micrometers thick on the front surface of the wafer such that devices can be fabricated directly on the epitaxial layer. Conventional epitaxial deposition processes are disclosed in U.S. Patent Nos. 5,904,769 and 5,769,942.

The epitaxial deposition process is typically comprised of two steps. In the  
25 first step after the semiconductor wafer is loaded into a deposition chamber and lowered onto a susceptor, the front surface of the wafer is subjected to a cleaning gas such as hydrogen or a hydrogen/hydrochloric acid mixture at about 1150°C to "pre-bake" and clean the front surface of the semiconductor wafer and remove any native oxide on that surface to allow the epitaxial silicon layer to grow continuously and  
30 evenly onto the front surface. In the second step of the epitaxial deposition process

the front surface of the wafer is subjected to a vaporous silicon source such as silane or trichlorosilane at about 800°C or higher to deposit and grow an epitaxial layer of silicon on the front surface. During both steps of the epitaxial deposition process the semiconductor wafer is supported in the epitaxial deposition chamber by the susceptor which is generally rotated during the process to ensure even growth of the epitaxial layer. The susceptor is generally comprised of high purity graphite and has a silicon carbide layer completely covering the graphite to reduce the amount of contaminants such as iron released from the graphite into the surrounding ambient during high temperature processes. Conventional susceptors used in epitaxial growth processes are well known in the art and described in U.S. Patent Nos. 4,322,592, 4,496,609, 5,200,157, and 5,242,501.

When a conventional susceptor is utilized in the epitaxial deposition process, during the loading process as the wafer is lowered onto the susceptor, gas can be trapped between the susceptor and the wafer causing the wafer to "float" and slide onto the susceptor in a tilted position. This can result in uneven epitaxial growth. Furthermore, during the pre-bake step a small amount of cleaning gas such as hydrogen can effuse around the wafer edge between the wafer and the susceptor and into the space between the wafer and the susceptor. If the back surface of the wafer is sealed with an oxide layer, such as a low temperature oxide layer, the effused hydrogen will not react sufficiently with the oxide layer to create pinholes in the layer or completely remove the oxide layer. If the back surface is an etched or polished surface as desired by many device manufacturers and only contains a thin native oxide layer, the hydrogen or hydrogen/hydrochloric acid mixture will completely remove the native oxide layer near the outer edge of the back surface where the cleaning gas effuses around the wafer and will create pinhole openings in the native oxide layer exposing the silicon surface as etching moves away from the outer edge of the wafer. These pinhole openings typically form a ring or "halo" around the wafer.

During the epitaxial deposition process a small amount of silicon containing source gas can also effuse around the wafer edge between the wafer and the susceptor and into space between the wafer and the susceptor. If the back surface of the wafer is oxide sealed, nucleation and growth of a silicon film is substantially suppressed. In

areas where the native oxide layer has been completely etched away by the cleaning gas a smooth continuous layer of silicon is grown. Where the cleaning gas has not completely removed the native oxide layer and pinholes have created exposed silicon, however, the silicon containing source gas can deposit silicon in the pinholes and  
5 create a non-uniform silicon film on the wafer backside during the epitaxial deposition. Thus, for wafers with etched or polished back surfaces having only a native oxide layer, pinholes created in the native oxide layer during the pre-bake step may lead to discontinuous silicon growth on the back surface which appears hazy under bright light illumination. This haziness or "halo" on the back surface of the  
10 wafer is comprised of small silicon growths or bumps having a diameter of about 0.5 micrometers and being about 10 nanometers high. These bumps of silicon scatter light and lead to the haziness and are undesirable as they can interfere with machine vision and optical pyrometry systems that view the back surface of the wafer during device processing.

15 Another problem encountered during the high temperature growth of the epitaxial silicon layer is the out-diffusion of dopant atoms such as boron or phosphorus through the back surface of the semiconductor wafer during the high temperature pre-bake and the epitaxial growth steps. With conventional susceptors, the dopant atoms that out-diffuse from the back surface are trapped between the  
20 susceptor and the wafer itself and can effuse between the wafer edge and the susceptor toward the front surface of the wafer. These dopant atoms can be incorporated into and contaminate the growing deposition layer and degrade the resistivity uniformity near the wafer edge. If the back surface of the semiconductor wafer is oxide sealed using for example, a low temperature oxide, the dopant atoms will not substantially  
25 out-diffuse from the back surface. Semiconductor wafers having etched or polished back surfaces, however, are subject to out-diffusion of dopant atoms from the back surface during the epitaxial deposition process which can lead to unwanted autodoping of the front surface.

Several methods have been suggested for attempting to eliminate back surface  
30 halos and autodoping. To eliminate back surface halos Nakamura (Japanese Unexamined Patent Application No. JP11-16844) disclosed performing a hydrogen

fluoride strip and/or a high-temperature hydrogen annealing step of the back surface up to 10 days before the wafers are loaded into the epitaxial reactor. The process adds additional processing steps which can greatly increase complexity and cost of the deposition process. Deaton et al. (U.S. Patent No. 5,960,555) disclosed a method of preventing the frontside reactive source gas from effusing to the wafer backside by  
5 utilizing a susceptor with built-in channels along the wafer edge for directing purge gas flows to the edge of the wafer. This process requires substantial modification of existing epitaxial deposition chambers and utilizes increased purge gas flows which can cause the purge gas to spill over to the front surface and mix with the source gas  
10 which can degrade the resulting epitaxial film.

To reduce autodoping, Hoshi (Japanese Unexamined Patent Application No. JP11-87250) disclosed using vacuum sucking on the edge of a susceptor to evacuate boron dopant on the edge of the susceptor and prevent autodoping. This process may affect wafer edge uniformity and thickness and requires substantial modification to  
15 existing epitaxial deposition systems. Nakamura (Japanese Unexamined Patent Application JP10-223545) disclosed a modified susceptor having slots on the edge of the susceptor such that the out-diffused dopant atoms would be pushed down through the slots and into the exhaust. This method also allows a substantial amount of the deposition gas to be evacuated below the back surface of the wafer which can lead to  
20 the halo affect previously discussed as well as premature corrosion of the exhaust system and safety concerns.

To date, the prior art fails to disclose satisfactory methods of controlling the halo effect on the back surface of semiconductors and autodoping problems associated with dopant out-diffusion from the back surface during an epitaxial deposition  
25 process. As such, a need exists in the semiconductor industry for a simple, cost effective approach to solving the halo effect and unwanted autodoping of the front surface of a semiconductor wafer during an epitaxial deposition process.

#### SUMMARY OF THE INVENTION

30 Among the objects of the present invention, therefore, are the provision of a modified susceptor which allows cleaning gas to contact substantially the entire back

surface of a semiconductor wafer; the provision of a modified susceptor which significantly reduces autodoping of the front surface of a semiconductor wafer during epitaxial silicon growth; the provision of a modified susceptor which allows substantially complete native oxide removal from the back surface of a semiconductor wafer during the pre-bake step of epitaxial deposition and substantially eliminates the halo affect; the provision of a modified susceptor having a plurality of holes such that epitaxial wafers produced using the susceptor are of improved quality; and the provision of a modified susceptor which reduces or eliminates wafer "floating" during loading.

10 Briefly, therefore, the present invention is directed to an apparatus for use in a chemical vapor deposition process wherein an epitaxial layer is grown on a semiconductor wafer. The apparatus comprises a susceptor sized and configured for supporting the semiconductor wafer. The susceptor has a surface having a density of openings between about 0.2 openings/cm<sup>2</sup> and about 4 openings/cm<sup>2</sup> which is in  
15 generally parallel opposed relationship with the wafer to permit fluid flow therethrough.

The invention is further directed to an apparatus for use in an epitaxial deposition process wherein an epitaxial layer is grown on a semiconductor wafer. The apparatus comprises a susceptor sized and configured for supporting the  
20 semiconductor wafer. The susceptor has a surface having a density of openings between about 0.5 openings/cm<sup>2</sup> and about 2 openings/cm<sup>2</sup> which is in generally parallel opposed relationship with the wafer to permit fluid flow therethrough. The apparatus further comprises a rotatable means for supporting the susceptor and the wafer, a heating element, an edge ring surrounding the periphery of the susceptor, and  
25 a gas inlet and a gas outlet.

The invention is further directed to a process for growing an epitaxial silicon layer on a semiconductor wafer. The process comprises introducing a cleaning gas into an epitaxial deposition chamber containing a wafer such that the gas flows parallel to the front and back surfaces and contacts the front surface of the wafer and  
30 substantially the back surface to remove a native oxide layer from the surfaces. After

the cleaning gas, a silicon containing source gas is introduced into the deposition chamber to grow an epitaxial silicon layer on the front surface

Other objects and features of this invention will be in part apparent and in part pointed out hereinafter.

## 5 BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a cross section of the modified susceptor of the present invention taken in the plane of line 1-1 of Fig. 2.

Fig. 2 is a top view of the modified susceptor of the present invention.

Fig. 3 is an epitaxial reaction chamber showing the modified susceptor of the present invention in cross section taken in the plane of line 1-1 of Fig. 2.

Fig. 4 is a cross section of a modified susceptor of the present invention.

Fig. 5 is a cross section of a modified susceptor of the present invention.

Corresponding reference characters indicate corresponding parts throughout the drawings.

## 15 DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

In accordance with the present invention, it has been discovered that high quality semiconductor wafers having an epitaxial silicon layer on the front surface can be produced utilizing an epitaxial deposition chamber incorporating a modified susceptor having a plurality of openings. Advantageously, the modified susceptor substantially eliminates "floating" during loading and allows fluid transport toward and away from the back surface of the wafer which allows the cleaning gas utilized in the pre-bake step of an epitaxial deposition process to contact substantially the entire back surface of the semiconductor wafer and chemically remove substantially the entire native oxide layer such that during the growth of the epitaxial layer when source gas contacts the back surface of the semiconductor wafer a smooth continuous layer of silicon is grown and the halo affect on the back surface is significantly reduced or eliminated. Furthermore, the modified susceptor allows dopant atoms contained in the semiconductor wafer that out-diffuse from the back surface of the



wafer during the epitaxial deposition process to be carried away from the front surface of the wafer in a purge gas stream and into the exhaust to keep a substantial amount of dopant from effusing between the wafer and the susceptor edge and contact the front surface resulting in unwanted autodoping of the front surface.

5           Referring now to the Figures, and more particularly to Fig. 1, there is shown a cross sectional view of the modified susceptor 2 of the present invention. Modified  
susceptor 2 has an inner annular ledge 22 which is capable of supporting  
semiconductor wafer 4 which has a front surface 6 and a back surface 8. Modified  
susceptor 2 has a porous surface 9 with a plurality of holes or openings 10, 11, 12, 13,  
10   14, 16, and 18 and wafer lift pin hole 21. The terms openings and holes may be used  
interchangeably herein and both refer to the open passageways in the porous surface  
9. Porous surface 9 having the openings is located directly below the semiconductor  
wafer 4. As used herein, the term "plurality" means two or more holes. Holes 10, 11,  
12, 13, 14, 16, and 18 are drilled into modified susceptor 2 prior to the coating being  
15   applied. During the pre-bake step of an epitaxial deposition process, holes 10, 11, 12,  
13, 14, 16, and 18 allow the cleaning gas to contact substantially the entire back  
surface 8 of semiconductor wafer 4 to allow the cleaning gas to react with, and  
remove substantially all native oxide on the back surface 8 of semiconductor wafer 4.  
The portion of back surface 8 of semiconductor wafer 4 in contact with the inner  
20   annular ledge 22 of susceptor 2 is also substantially etched by the cleaning gas as the  
gas will effuse between the wafer and the susceptor resulting in substantially complete  
removal of the native oxide layer on the back surface. The removal of the native  
oxide from the back surface 8 significantly reduces or eliminates any halo effect on  
the back surface of the semiconductor wafer as any source gas that effuses between  
25   the wafer and the susceptor during the epitaxial growth process and contacts back  
surface 8 will grow smoothly and continuously on top of the silicon surface. Holes  
10, 11, 12, 13, 14, 16, and 18 also allow dopant atoms that out-diffuse from the back  
surface 8 of semiconductor wafer 4 during the high temperature cleaning step and  
epitaxial deposition step of an epitaxial deposition process to drain through the holes  
30   into a purge gas or hydrogen stream and away from the front surface 6 of

semiconductor wafer 4 into the exhaust system. As such, a significant reduction in autodoping of the front surface during an epitaxial deposition process is realized.

Referring now to Fig. 2, there is shown a top view of modified susceptor 2 having inner annular ledge 22 and porous surface 24 having a plurality of holes.

5 Wafer lift pin holes 28, 30, and 32 on porous surface 24 allow lift pins (not shown) below the modified susceptor 2 to raise and lower semiconductor wafers onto and off of the modified susceptor during and after an epitaxial deposition process. Edge ring 26 surrounds the periphery of modified susceptor 2 and is utilized throughout an epitaxial deposition process to ensure temperature uniformity across a semiconductor  
10 wafer such that a temperature gradient does not form across the wafer and adversely affect the deposition process. Edge ring 26 generally has a diameter 4 centimeters to about 10 centimeters greater than the diameter of modified susceptor 2 and is comprised of high purity graphite which has a silicon carbide or glassy carbon coating.

15 The modified susceptor of the present invention can be sized and configured such that the inner annular ledge of the susceptor can accommodate any diameter semiconductor wafer including, for example, 150 millimeter, 200 millimeter and 300 millimeter wafers. The modified susceptor may be constructed of conventional materials such as high purity graphite and has a silicon carbide or glassy carbon layer  
20 covering the graphite to reduce the amount of contaminants released into the surrounding ambient from the graphite during the high temperature epitaxial deposition process. The graphite utilized to construct the susceptor is generally at least about 99%, more preferably at least about 99.9% and most preferably at least about 99.99% pure graphite. Also, the graphite preferably contains less than about 20  
25 ppm total metals such as iron, molybdenum, copper, and nickel, and more preferably less than about 5 ppm total metals such as iron, molybdenum, copper, and nickel. The silicon carbide or glassy carbon coating covering the graphite generally has a thickness of between about 75 micrometers and about 150 micrometers, preferably about 125 micrometers.

30 The holes in the porous surface of the modified susceptor located directly below the semiconductor wafer preferably have a diameter such that the silicon

carbide or glassy carbon coating, if applied to the susceptor after the holes have been drilled into the susceptor, will not substantially block or plug the holes and thus restrict fluid flow therethrough. It will be recognized by one skilled in the art that the openings, generally referred to as holes throughout, could be squares, slots, diamond shapes, or any other shapes allowing fluid flow therethrough. The openings preferably have a width of between about 0.1 millimeters and about 3 millimeters, more preferably between about 0.1 millimeters and about 1 millimeter, and most preferably between about 0.5 millimeters and about 1 millimeter. The width of the openings is defined as the greatest distance between two corners of the opening or the diameter if the opening is a circle. The holes are spaced on the modified susceptor to allow the cleaning gas utilized during the pre-bake step of the epitaxial deposition process to contact and etch substantially the entire back surface of the semiconductor wafer. Spacing of the holes of the modified susceptor of between about 0.5 millimeters and about 4 centimeters apart, more preferably between about 2 millimeters and about 2 centimeters apart, and most preferably between about 6 millimeters and about 1.5 centimeters apart allows the cleaning gas to contact substantially the entire back surface of the semiconductor wafer such that it may etch substantially all of the native oxide from the back surface. The total percentage of open area on the surface of the susceptor is between about 0.5% and about 4% of the total surface area of the susceptor, more preferably between about 1% and about 3% of the total surface area of the susceptor. The surface of the susceptor preferably has a density of between about 0.2 holes/cm<sup>2</sup> and about 4 holes/cm<sup>2</sup>, more preferably between about 0.8 holes/cm<sup>2</sup> and about 1.75 holes/cm<sup>2</sup>. Density as used herein means either a uniform or non-uniform density.

It is generally preferred that the holes in the modified susceptor have as small a diameter as practical yet not allow the silicon carbide or glassy carbon coating to restrict fluid flow through the holes to the back surface of the semiconductor wafer. If the holes in the susceptor are drilled too large, nanotopology problems on the front surface of the wafer that are caused by localized temperature non-uniformity on the back surface can occur. Large diameter holes in the modified susceptor can lead to the development of hot spots or cold spots on the back surface of the semiconductor

wafer through direct irradiation of the back surface by the heating lamps located below the semiconductor wafer. These hot or cold spots cause temperature gradients to form across the front surface of the semiconductor wafer and can lead to non-uniform epitaxial silicon growth on the front surface of the semiconductor wafer.

- 5 Non-uniform growth of the epitaxial layer significantly degrades the wafer quality. The holes on the modified susceptor can be drilled into the susceptor at an oblique angle to further reduce the possibility of direct irradiation of the back surface by the heating lamps and the formation of hot or cold spots leading to non-uniform epitaxial growth on the front surface yet still allow gases to penetrate the susceptor and contact
- 10 the back surface and allow out-diffused dopant atoms to move away from the back surface. To further decrease the potential for the formation of hot or cold spots and the creation of temperature gradients on the semiconductor wafer by direct illumination of the wafer through the holes and reduce or eliminate any hot or cold spots caused by the lift pin holes, the lamp power ratio of the heating lamps above and
- 15 below the semiconductor wafer can be adjusted and tuned to produce a balanced heating from the lamps.

The modified susceptor of the present invention may be utilized as part of an apparatus for chemical vapor deposition processes such as an epitaxial deposition processes. Referring now to Fig. 3, there is shown an epitaxial reaction chamber 34

20 for use during an epitaxial growth process utilizing the modified susceptor 36 of the present invention. Modified susceptor 36 is attached to rotatable support means 58 and 59 and is sized and configured to support semiconductor wafer 38 on inner annular ledge 42 during an epitaxial deposition process. Semiconductor wafer 38 is in spaced relationship with holes 44, 45, 46, 47, 48, 49, and 51 in porous surface 49 in

25 modified susceptor 36. Lift pin hole 62 allows a lift pin (not shown) access through porous surface 9 of modified susceptor 36 to semiconductor wafer 38 such that semiconductor wafer 38 may be lifted onto and off of modified susceptor 36 before and after an epitaxial deposition process. Epitaxial deposition chamber 34 also contains heating lamp arrays 50 and 52 located above and below modified susceptor

30 36 respectively for heating during an epitaxial deposition process. Gas inlets 54 and 56 allow the introduction of the cleaning gas during the prebake step of the epitaxial

deposition process such that cleaning gas is introduced above and below the semiconductor wafer 38 to enhance the native oxide removal of the front surface 60 and back surface 62 of semiconductor wafer 38. During the epitaxial growth step, gas inlet 54 introduces a silicon containing source gas which is flowed above the wafer 38 and gas inlet 56 introduces hydrogen or an inert gas below the wafer 38 to flush the back surface 62 of the semiconductor wafer 38 and carry out-diffused dopant atoms away from the front surface. As indicated in Fig. 3, the gas injected into the epitaxial deposition chamber flows parallel to the front and back surfaces of the semiconductor wafer. Such a flow pattern allows the injected gases to contact the front surface and penetrate the susceptor through the holes in the susceptor's surface to contact the back surface of the wafer. Because the gases flow parallel to the semiconductor surfaces and not perpendicular, the possibility of the semiconductor wafer being lifted off of the annular ledge by gasses effusing between the wafer edge and edge of the annular ledge and becoming deformed is significantly reduced or eliminated. Gases introduced into chamber 34 from gas inlets 54 and 56 are removed from chamber 34 through exhaust port 64.

The holes in the modified susceptor will allow the cleaning gas to pass through the modified susceptor and contact substantially the entire back surface of the semiconductor wafer during the cleaning step such that any native oxide present on the back surface will be removed by the cleaning gas. This native oxide removal from the back surface will allow a smooth, continuous epitaxial silicon layer to grow on any portion of the back surface of the semiconductor wafer that is contacted with the source gas during the growth of the epitaxial layer and thus will substantially eliminate the formation of any halo on the back surface. Furthermore, the holes in the modified susceptor will allow inert gas or hydrogen to contact the back surface of the wafer such that dopant atoms that out-diffuse from the back surface during both the cleaning step and the epitaxial growth step may be carried away from the semiconductor wafer and into the exhaust thus substantially decreasing the possibility of autodoping the front surface of the wafer.

The epitaxial reaction chamber containing the modified susceptor of the present invention described above may be utilized for both the cleaning and the

growth steps of an epitaxial deposition process. In one epitaxial deposition process in accordance with the present invention, an epitaxial silicon layer is grown on the front surface of a semiconductor wafer. In a preferred embodiment of the present invention, a silicon wafer is introduced into an epitaxial deposition chamber at ambient pressure and a cleaning gas such as hydrogen or a mixture of hydrogen and hydrochloric acid is introduced into the chamber at a temperature of between about 1000°C and about 1300°C at a flow rate of between about 1 liter/minute and about 50 liters/minute, preferably between about 10 liters/minute and about 20 liters/minute for at least about 10 seconds to remove the native oxide layers on the front and back surfaces of the semiconductor wafer.

Once the native oxide layers have been removed from both the front and back surfaces of the semiconductor wafer, the cleaning gas is discontinued and the temperature in the reaction chamber is adjusted to between about 600°C and about 1200°C and a silicon containing source gas such as silane or dichlorosilane, for example, is introduced above the front surface of the semiconductor wafer at a flow rate of between about 1 liter/minute and about 20 liters/minute for a period of time sufficient to grow an epitaxial silicon layer on the front surface of the semiconductor wafer having a thickness of between about 0.1 and about 200 micrometers, preferably between about 1 and about 100 micrometers. At the same time the silicon containing source gas is introduced into the deposition chamber above the front surface of the semiconductor wafer, a gas such as nitrogen, argon, hydrogen, a mixture thereof or the source gas is introduced below the back surface of the semiconductor wafer at a flow rate of between about 1 liter/minute and about 50 liters/minute, preferably between about 10 liters/minute and about 20 liters/minute such that the purge gas can contact the back surface of the semiconductor wafer and carry out-diffused dopant atoms from the back surface toward to the exhaust outlet. This preferred embodiment significantly reduces or eliminates any back surface halo effect and minimizes autodoping of the front surface. Although the preferred epitaxial deposition process is carried out at ambient pressure, reduced pressure chemical vapor deposition is also within the scope of the present invention.

In an alternative embodiment of the present invention, the modified susceptor may be sized and configured to allow the semiconductor wafer to rest directly on the porous surface thus eliminating the inner annular ledge 22 as shown in Fig. 1.

Referring now to Fig. 4, there is shown a cross section of a modified susceptor where the semiconductor wafer rests directly upon the porous surface. The back surface 76 of semiconductor wafer 70 sits directly on porous surface 72 of modified susceptor 74. Although back surface 76 of wafer 70 is in direct contact with the porous surface 72, gases flowed beneath modified susceptor 74 are able to penetrate porous surface 72 through holes 78, 80, 82, 84, 86, 88, and 90 and contact substantially the entire back surface 76 of wafer 70.

In a further alternative embodiment, the modified susceptor of the present invention as illustrated in Fig. 4 may be further modified such that porous surface 72 is shaped in a dish or dome shape to allow only the outer edges of the semiconductor wafer to contact the modified susceptor. Referring now to Fig. 5, there is shown a cross section of a modified susceptor where the semiconductor wafer rests directly on the porous surface of the susceptor. The back surface 76 of semiconductor wafer 70 sits directly on porous surface 72 of modified susceptor 74. Porous surface 72 is shaped like a dish or dome such that the outer edges 92 and 94 of semiconductor wafer 70 are in direct contact with the porous surface 72 and the remainder of back surface 76 of wafer 70 is not in direct contact with porous surface 72. During use, holes 78, 80, 82, 84, 86, 88, and 90 allow fluid flow therethrough to the back surface of the wafer.

It will be recognized by one skilled in the art that the modified susceptor of the present invention can be utilized with various types of deposition reactors including barrel, pancake and mini batch reactors regardless of the shape of the susceptor utilized.

In view of the above, it will be seen that the several objects of the invention are achieved. As various changes could be made in the above-described modified susceptor without departing from the scope of the invention, it is intended that all matter contained in the above description be interpreted as illustrative and not in a limiting sense.

## WHAT IS CLAIMED IS:

1. An apparatus for use in a chemical vapor deposition process wherein an epitaxial silicon layer is grown on a semiconductor wafer, the semiconductor wafer having a front surface and a back surface, the apparatus comprising:  
a susceptor sized and configured for supporting the semiconductor wafer  
5 thereon, the susceptor having a surface having a density of openings between about 0.2 openings/cm<sup>2</sup> and about 4 openings/cm<sup>2</sup>, the surface being in a generally parallel opposed relationship with the semiconductor wafer to permit fluid flow therethrough for fluid contact with the back surface of the semiconductor wafer.
2. Apparatus set forth in claim 1 wherein the susceptor has lift pin holes in the surface having the plurality of openings to allow lift pins to pass through the susceptor.
3. Apparatus set forth in claim 1 wherein the openings have a diameter of between about 0.1 millimeters and about 3 millimeters.
4. Apparatus set forth in claim 1 wherein the openings have a diameter of between about 0.1 millimeters and about 1 millimeter.
5. Apparatus set forth in claim 1 wherein the openings are spaced between about 2 millimeters and about 2 centimeters apart.
6. Apparatus set forth in claim 1 wherein the surface has between about 0.8 openings/cm<sup>2</sup> and about 1.75 openings/cm<sup>2</sup>.
7. An apparatus for use in an epitaxial deposition process wherein an epitaxial silicon layer is grown on a semiconductor wafer, the semiconductor wafer having a front surface and a back surface, the apparatus comprising:



a susceptor sized and configured for supporting the semiconductor wafer  
5 thereon, the susceptor having a surface having a density of openings of between about 0.5 openings/cm<sup>2</sup> and about 2 openings/cm<sup>2</sup>, the surface being in a generally parallel opposed relationship with the semiconductor wafer to permit fluid flow therethrough for fluid contact with the semiconductor wafer;

rotatable means for supporting the susceptor and semiconductor wafer;  
10 a heating element;  
an edge ring surrounding the periphery of the susceptor;  
a gas inlet for allowing cleaning gas and source gas to enter the apparatus; and  
a gas outlet for removing cleaning gas and source gas from the apparatus.

8. Apparatus set forth in claim 7 wherein the total percentage of open area on the surface is between about 0.5% and about 4%.

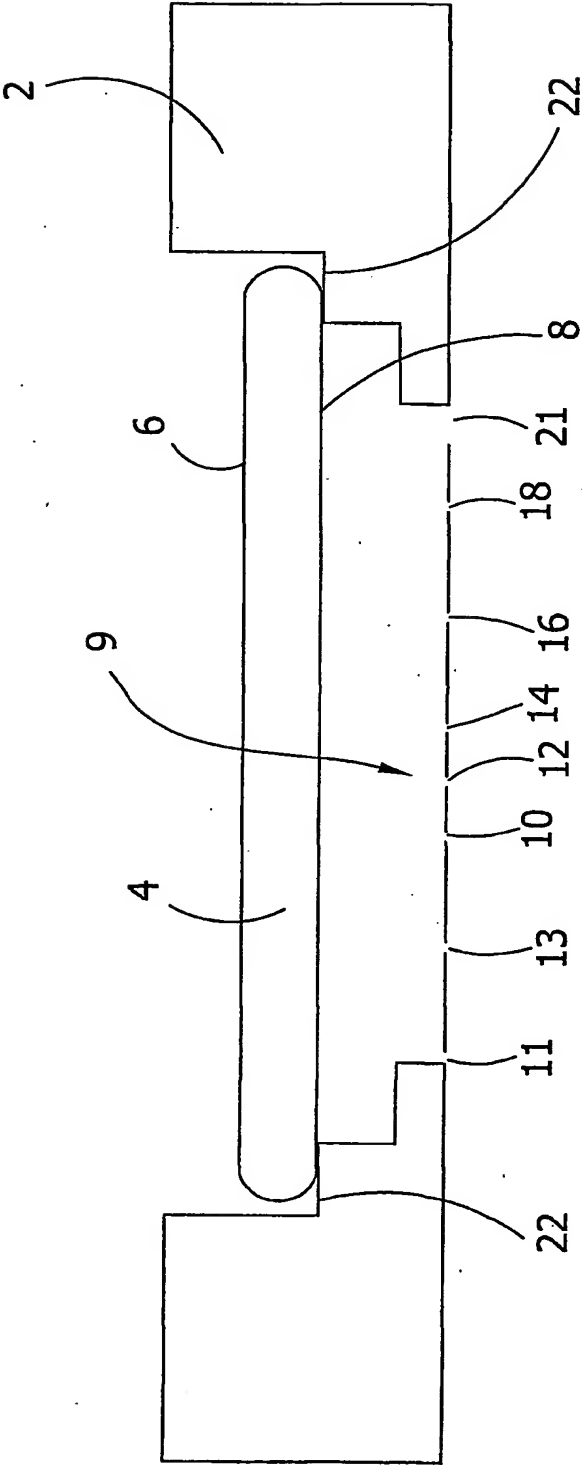
9. A process for growing an epitaxial silicon layer on a semiconductor wafer, the semiconductor wafer having a front surface and a back surface, the process comprising:

introducing a cleaning gas into an epitaxial deposition chamber containing the  
5 semiconductor wafer such that the cleaning gas flows parallel to the front and back surfaces and contacts the front surface of the semiconductor wafer and substantially the entire back surface of the semiconductor wafer to remove a native oxide layer from the front surface and the back surface of the semiconductor wafer; and

introducing a silicon containing source gas into the epitaxial deposition  
10 chamber to grow an epitaxial silicon layer on the front surface of the semiconductor wafer while introducing a purge gas into the epitaxial deposition chamber to remove out-diffused dopant atoms from the back surface of the semiconductor wafer away from the front surface of the semiconductor wafer.

10. The process as set forth in claim 9 wherein the epitaxial layer is between about 0.1 micrometer and about 200 micrometers thick.

FIG. 1



2/5

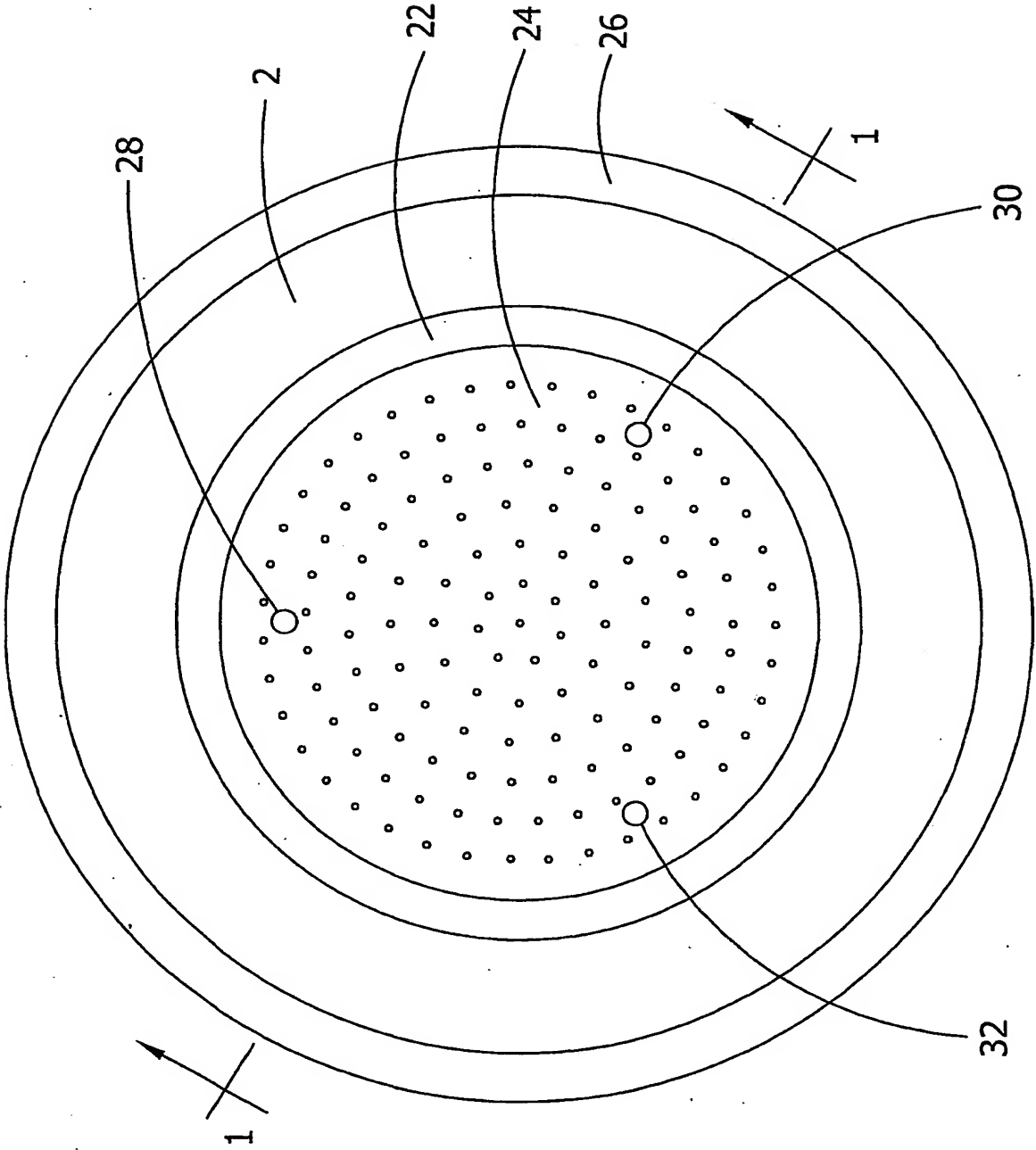
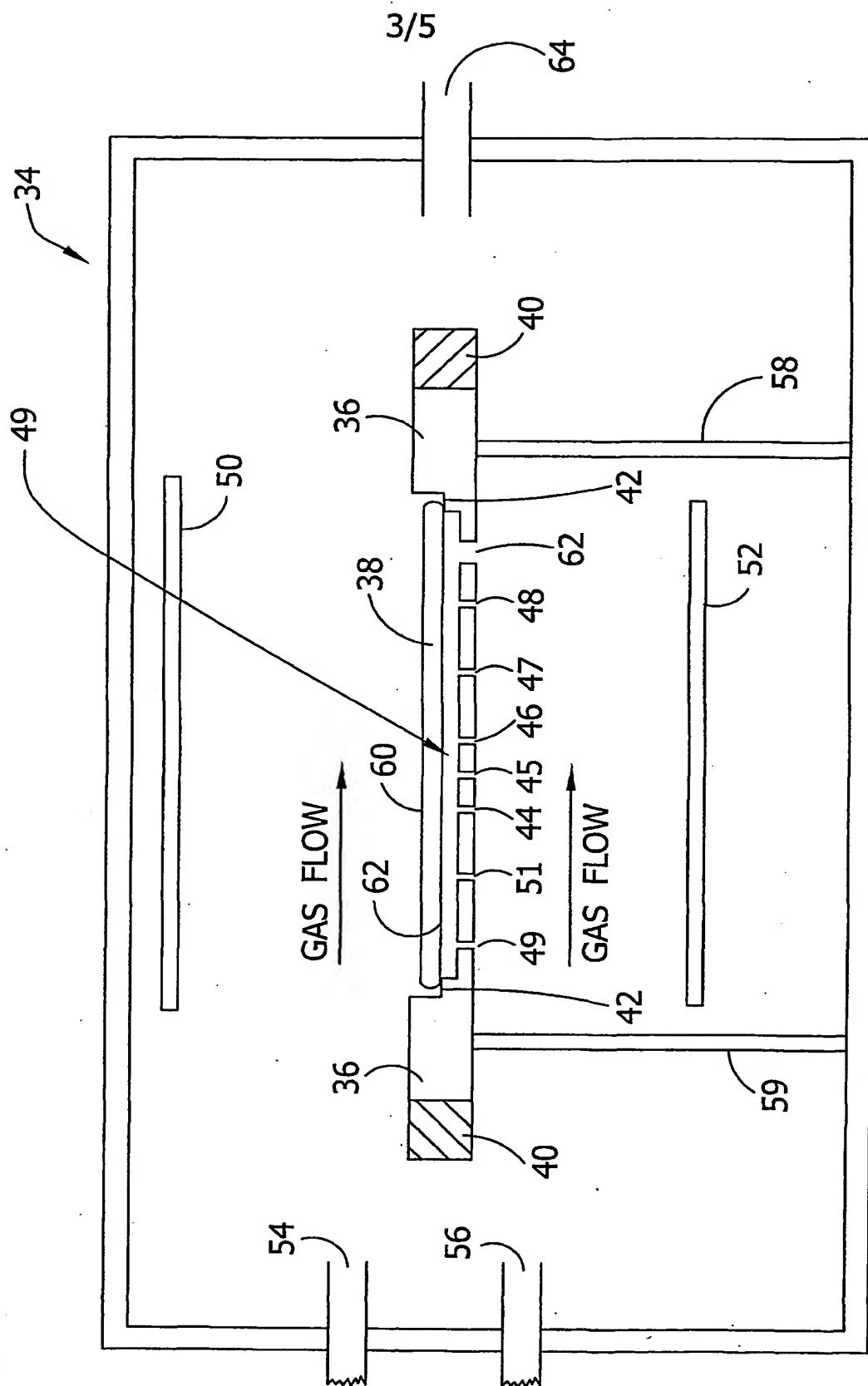


FIG. 2

FIG. 3



5/5

FIG. 5

